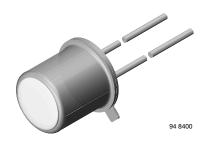
## Vishay Semiconductors



# Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



### **DESCRIPTION**

TSTA7500 is an infrared, 875 nm emitting diode in GaAlAs technology in a hermetically sealed TO-18 package with flat glass window.

### **FEATURES**

Package type: leaded
Package form: TO-18
Dimensions (in mm): Ø 4.7
Peak wavelength: λ<sub>p</sub> = 875 nm

High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity:  $\phi = \pm 30^{\circ}$ 

• Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



· Radiation source near infrared range

| PRODUCT SUMMARY |                        |         |                     |                     |  |
|-----------------|------------------------|---------|---------------------|---------------------|--|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (deg) | λ <sub>P</sub> (nm) | t <sub>r</sub> (ns) |  |
| TSTA7500        | 6                      | ± 30    | 875                 | 600                 |  |

#### Note

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |  |  |
|----------------------|-----------|------------------------------|--------------|--|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |  |
| TSTA7500             | Bulk      | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18        |  |  |

### Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS            |                                    |                   |               |      |  |
|-------------------------------------|------------------------------------|-------------------|---------------|------|--|
| PARAMETER                           | TEST CONDITION                     | SYMBOL            | VALUE         | UNIT |  |
| Reverse voltage                     |                                    | V <sub>R</sub>    | 5             | V    |  |
| Forward current                     |                                    | I <sub>F</sub>    | 100           | mA   |  |
| Peak forward current                | $t_p/T = 0.5, t_p \le 100 \ \mu s$ | I <sub>FM</sub>   | 200           | mA   |  |
| Surge forward current               | t <sub>p</sub> ≤ 100 μs            | I <sub>FSM</sub>  | 2.5           | Α    |  |
| Dower discination                   |                                    | P <sub>V</sub>    | 180           | mW   |  |
| Power dissipation —                 | T <sub>case</sub> ≤ 25 °C          | P <sub>V</sub>    | 500           | mW   |  |
| Junction temperature                |                                    | Tj                | 100           | °C   |  |
| Storage temperature range           |                                    | T <sub>stg</sub>  | - 55 to + 100 | °C   |  |
| Thermal resistance junction/ambient | leads not soldered                 | R <sub>thJA</sub> | 450           | K/W  |  |
| Thermal resistance junction/case    | leads not soldered                 | R <sub>thJC</sub> | 150           | K/W  |  |

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified





ROHS



# Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs

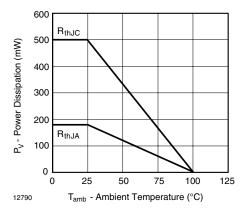


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

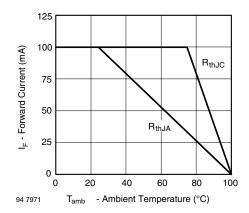


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS               |   |                  |      |       |      |       |
|-------------------------------------|---|------------------|------|-------|------|-------|
| PARAMETER                           | TEST CONDITION  | SYMBOL           | MIN. | TYP.  | MAX. | UNIT  |
| Forward voltage                     | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$               | $V_{F}$          |      | 1.4   | 1.8  | V     |
| Breakdown voltage                   | I <sub>R</sub> = 100 μA                                     | $V_{(BR)}$       | 5    |       |      | V     |
| Junction capacitance                | $V_R = 0 \text{ V, f} = 1 \text{ MHz, E} = 0$               | C <sub>j</sub>   |      | 20    |      | pF    |
| Radiant intensity                   | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$               | I <sub>e</sub>   | 3.5  | 6     | 16   | mW/sr |
| Radiant power                       | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$               | фе               |      | 10    |      | mW    |
| Temperature coefficient of $\phi_e$ | I <sub>F</sub> = 100 mA                                     | TKφ <sub>e</sub> |      | - 0.7 |      | %/K   |
| Angle of half intensity             |   | φ                |      | ± 30  |      | deg   |
| Peak wavelength                     | I <sub>F</sub> = 100 mA                                     | $\lambda_{p}$    |      | 875   |      | nm    |
| Spectral bandwidth                  | I <sub>F</sub> = 100 mA                                     | Δλ               |      | 80    |      | nm    |
| Disching                            | I <sub>F</sub> = 100 mA                                     | t <sub>r</sub>   |      | 600   |      | ns    |
| Rise time                           | $I_F = 1.5 \text{ A}, t_p/T = 0.01, t_p \le 10 \mu\text{s}$ | t <sub>r</sub>   |      | 300   |      | ns    |
| Virtual source diameter             |   | d                |      | 0.5   |      | mm    |

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

#### **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

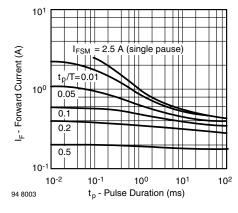


Fig. 3 - Pulse Forward Current vs. Pulse Duration

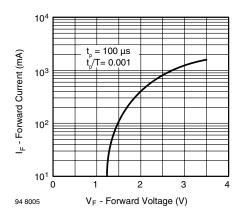


Fig. 4 - Forward Current vs. Forward Voltage

# Vishay Semiconductors Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



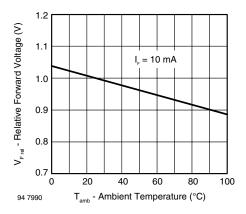


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

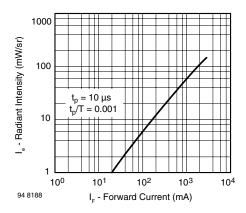


Fig. 6 - Radiant Intensity vs. Forward Current

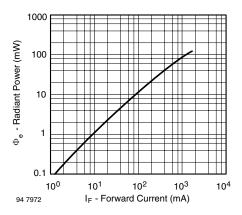


Fig. 7 - Radiant Power vs. Forward Current

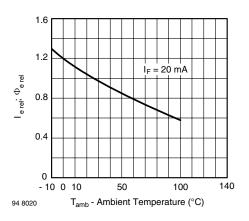


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

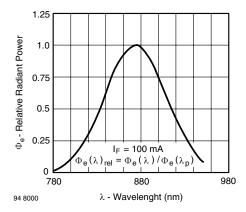


Fig. 9 - Relative Radiant Power vs. Wavelength

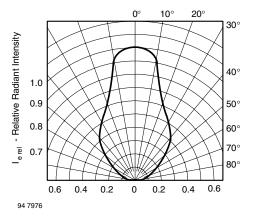
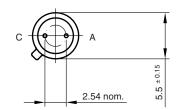


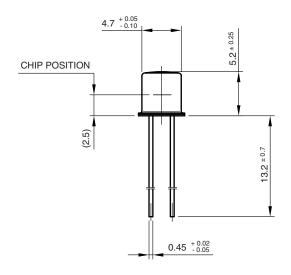
Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

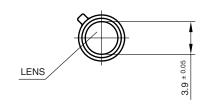


# Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs

## **PACKAGE DIMENSIONS** in millimeters









technical drawings according to DIN specifications

Drawing-No.: 6.503-5001.01-4

Issue: 2; 24.08.98

96 12173



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Vishay

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